

CDW COLLECTIVE MOTION IN 2D SYSTEMS

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in collaboratin with

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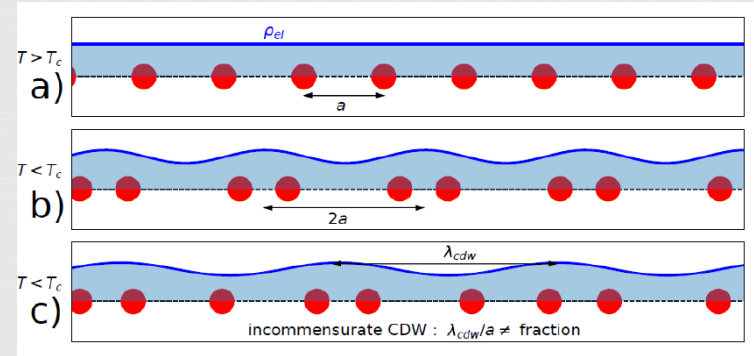
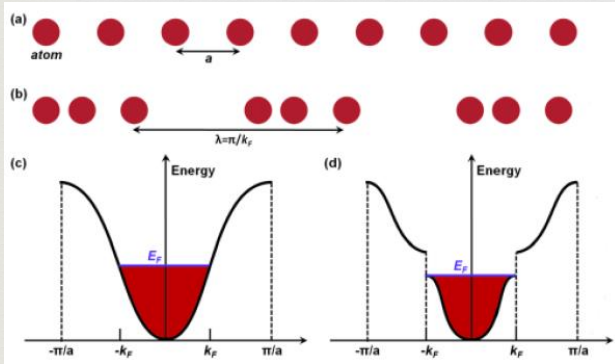
A. Frolov, A. Orlov and D. Voropaev

(Kotelnikov IRE RAS, Moscow)

OUTLINE:

1. CDW sliding, what is it and how it looks in 1D compounds
2. Main 2D systems revealing the CDW ordering.
3. Searching for the CDW sliding in TMD and QH systems
4. CDW sliding in compounds $R\text{Te}_3$ family.
Comparison with 1D case
5. “Time” effect
6. Conclusion

TRANSITION TO THE CDW STATE (1D CASE)



$$\rho(x) = \rho_0 \cos(Q \cdot x + \phi(x))$$

IN ELECTRIC FIELD

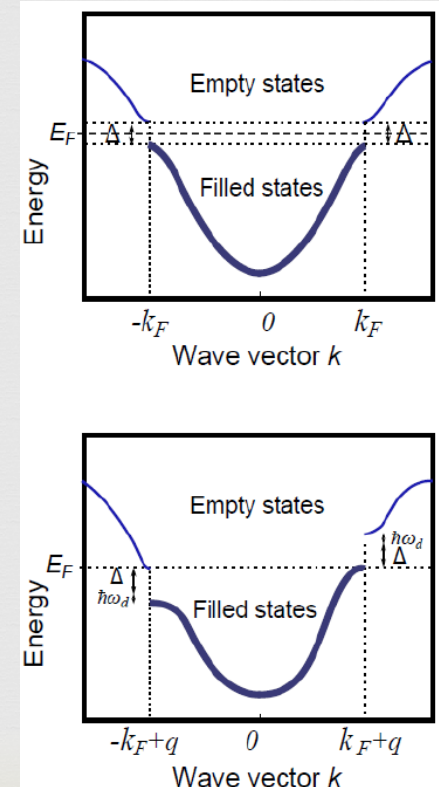
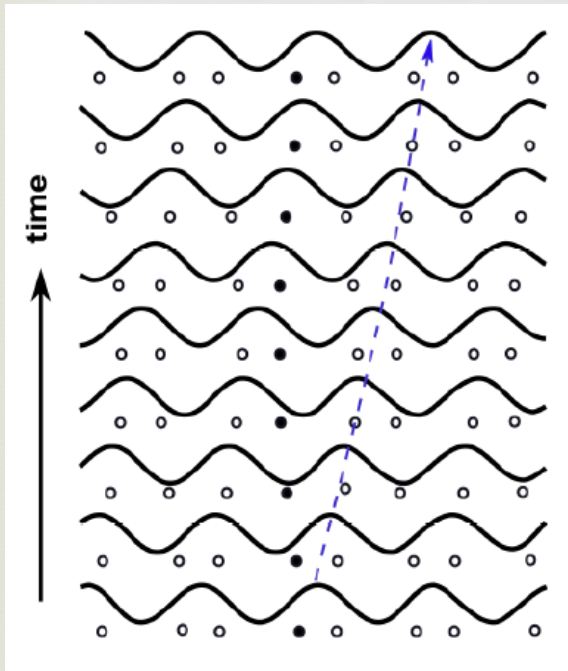
$$q = m_b V_d / \hbar$$

New FS sheets

$$(-\pi/k_F) + q$$

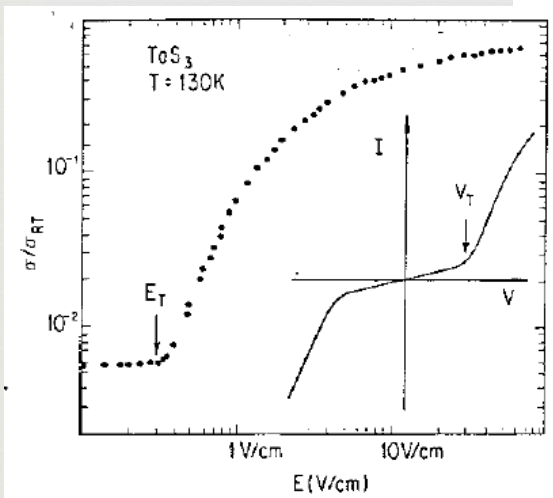
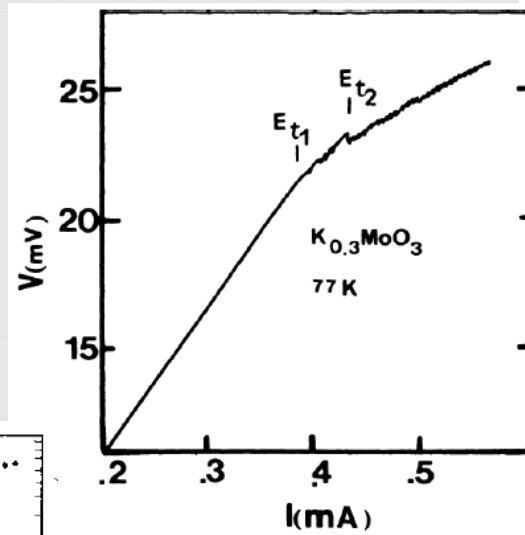
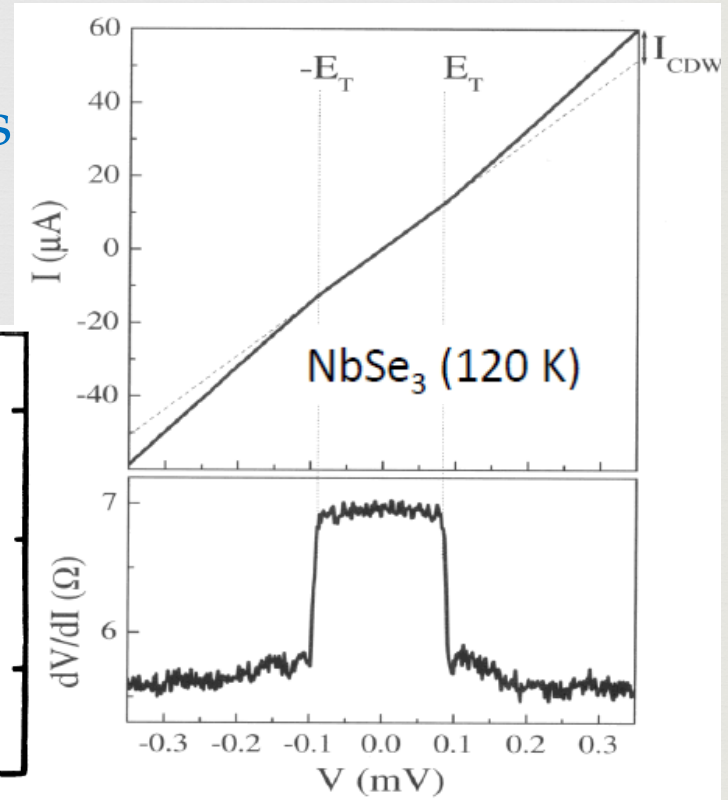
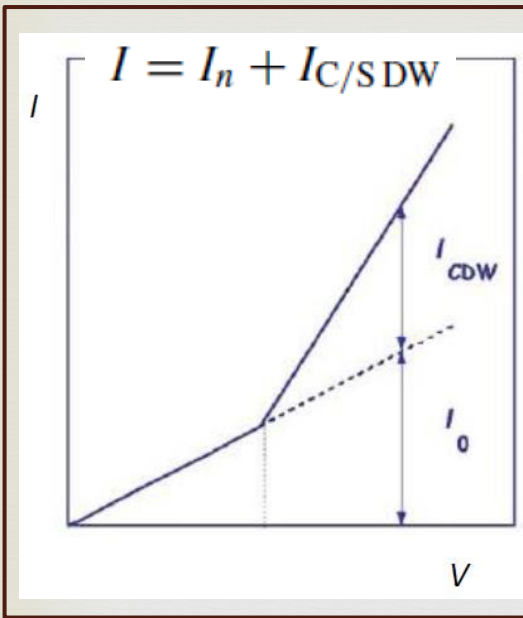
$$(+\pi/k_F) + q$$

$$\langle J_{CDW} \rangle = -n_c(0) e V_d$$



HOW IT LOOKS IN EXPERIMENT

dc IV characteristics

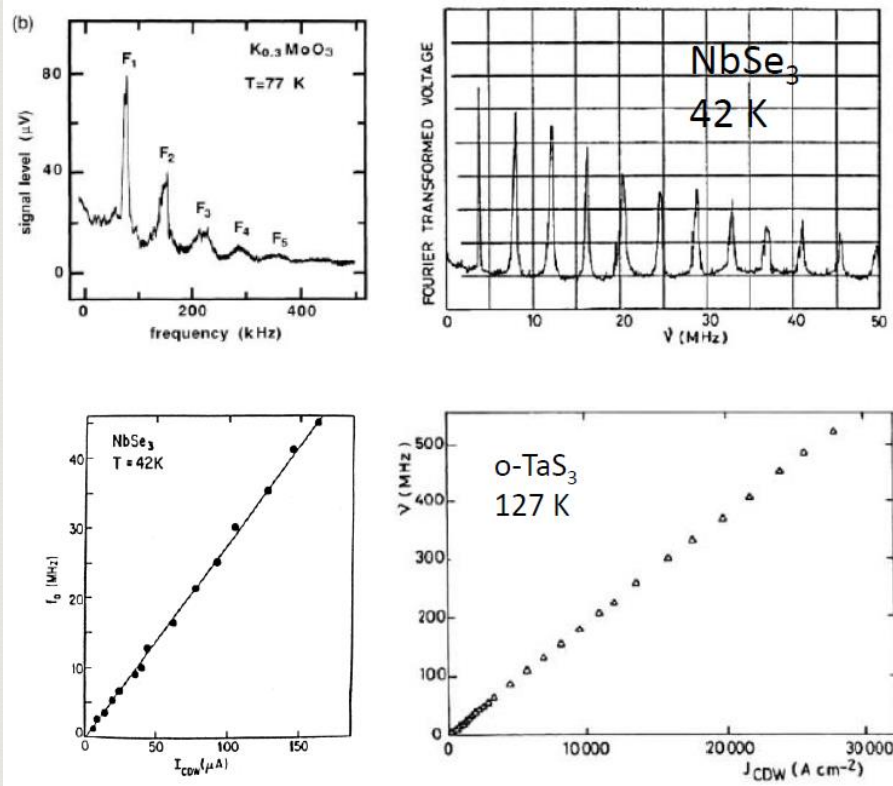


Sharp drop of differential resistance at threshold electric field

HOW IT LOOKS IN EXPERIMENT

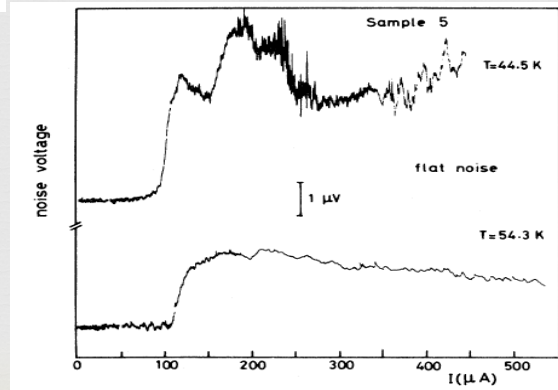
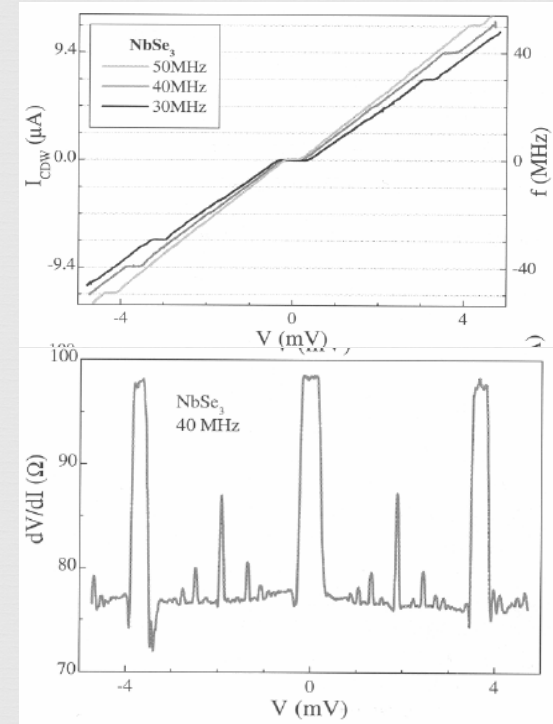
Narrow band noise

Shapiro steps



P. Monceau (1990)

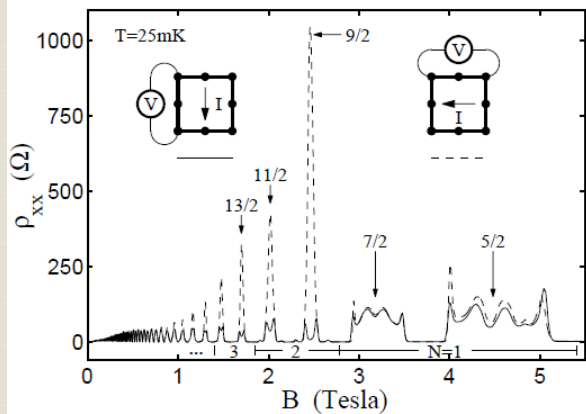
Broad band noise



P. Monceau (1982)

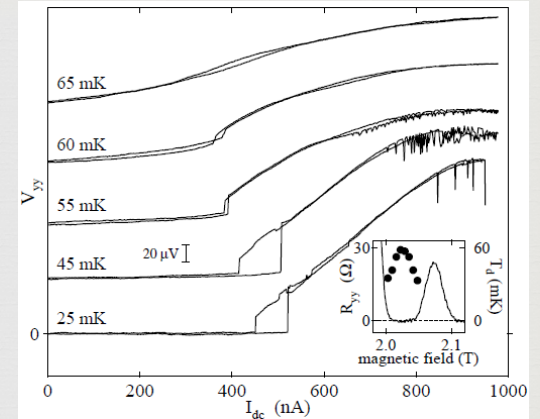
**MAIN 2D SYSTEMS REVEALING THE CDW ORDERING
(AND SLIDING?)**

GaAs/AlGaAs heterostructures



M. P. Lilly, et al., *Phys. Rev. Lett.* 82, 394 (1999)

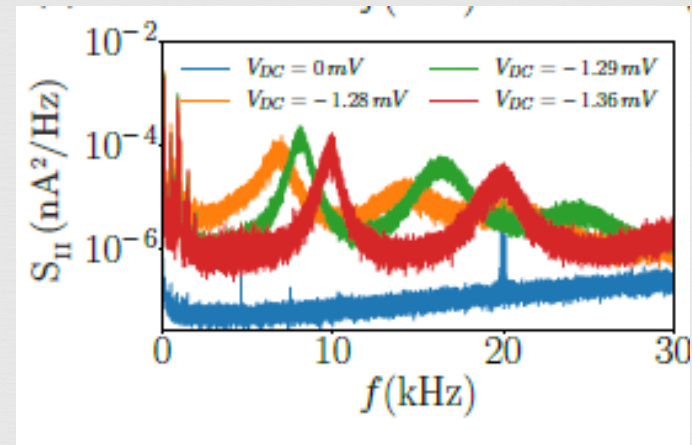
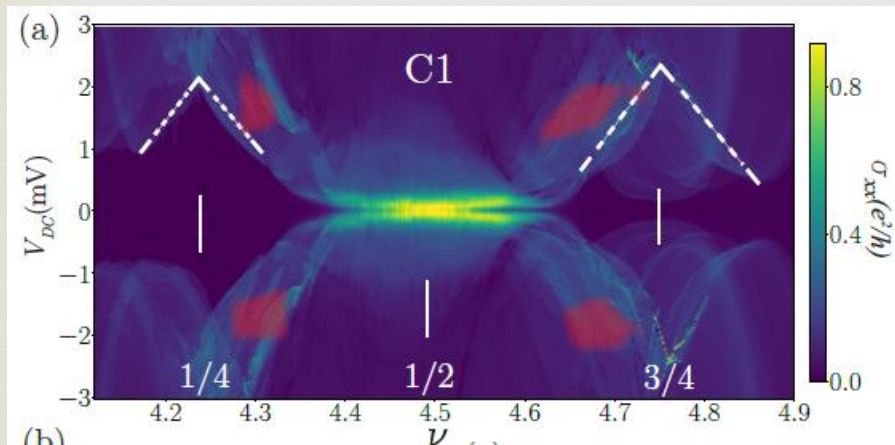
Near half-integer Landau fillings $\nu = 9/2; 11/2; 13/2$ with Landau levels $N > 1$ at certain current a sharp transition to a conducting state is observed. These phenomena are suggestive of the depinning of a charge density wave state.



K. B. Cooper, et al., *PRB* 60, R11285 (1999)

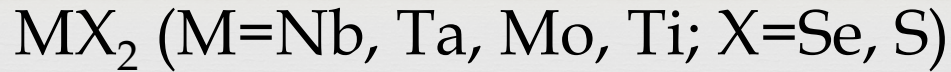
The same effect in Corbino geometry

K. Bennaceur, et al., *Phys. Rev. Lett.*, 120, 136801 (2018)



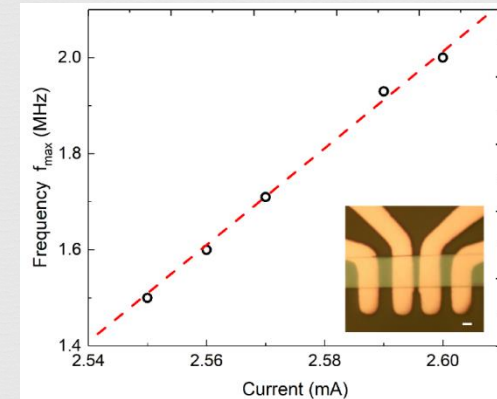
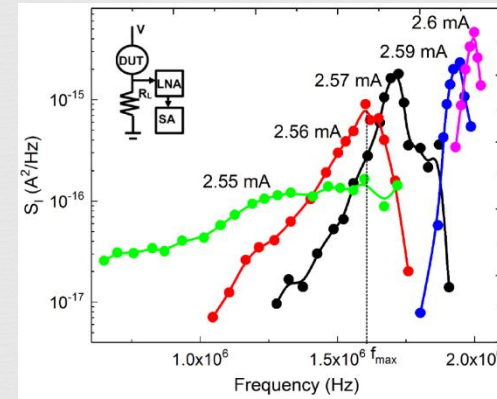
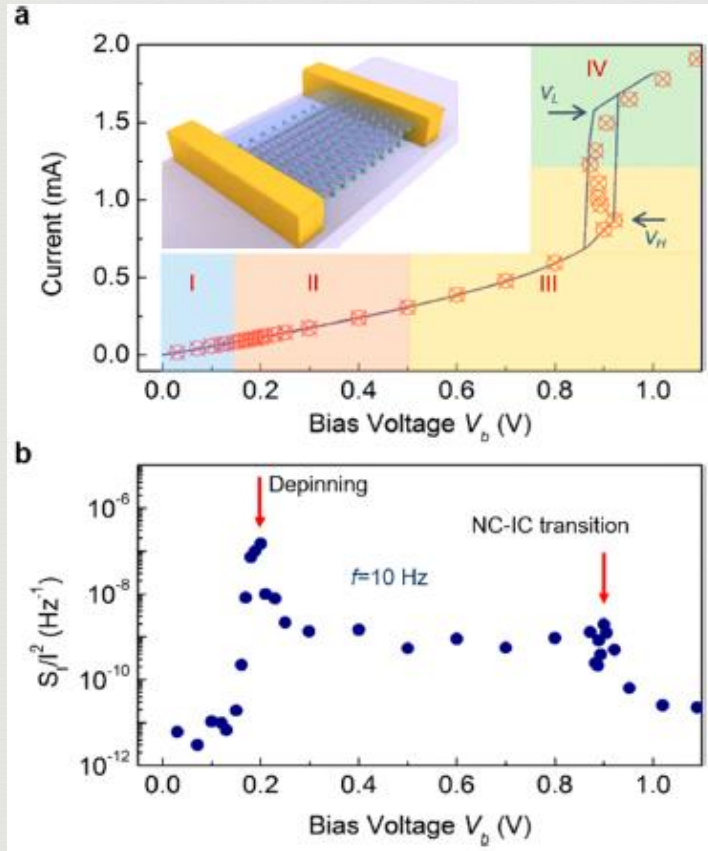
However, the frequency of periodic voltage is much lower than that originating from the sliding CDW picture

Transition metal dichalcogenides (TMDC)



BBN in 1T-TaS₂

NBN in 1T-TaS₂



G. Liu, et al., *Nano Lett.*, 18, 3630 (2018) A. Mohammadzadeh, et al., *Appl. Phys. Lett.* 118, 223101 (2021).

No direct contribution of the CDW motion (if it is motion).

Some indication of sliding-like effects also in

*2D organic compounds
manganites*

(T. Mori, et al., Phys. Rev. B 79, 115108 (2009))

(A.Wahl, et al., Phys. Rev. B 68, 094429 (2003))

but...

Now we know only one family of compounds which demonstrates all characteristic features of the CDW sliding

RTe₃ (R = Y, La, Ce, Nd, Sm, Gd, Tb, Ho, Dy, Er, Tm)

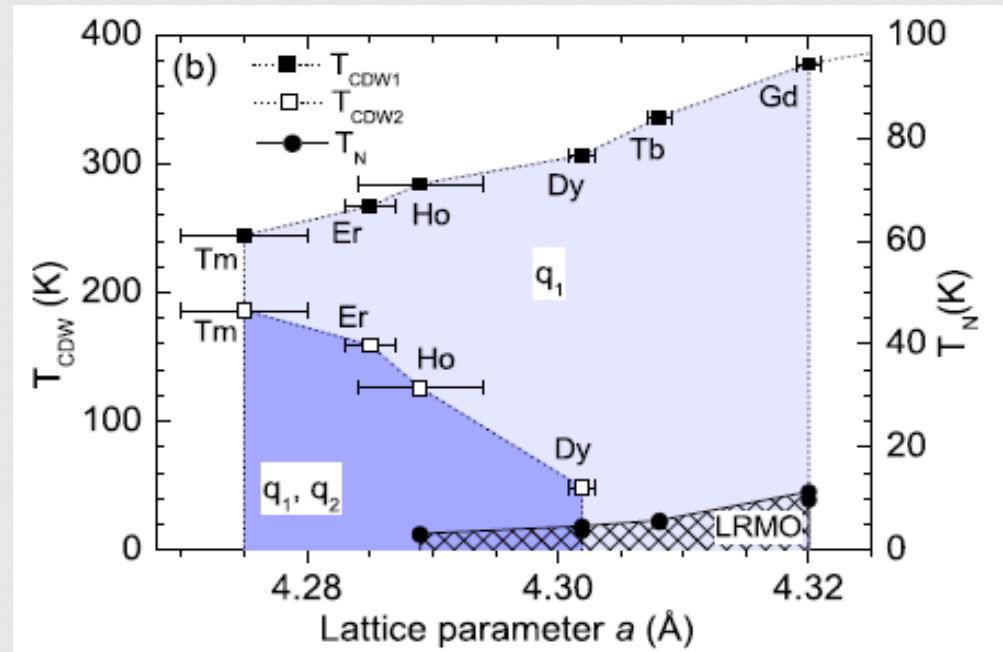
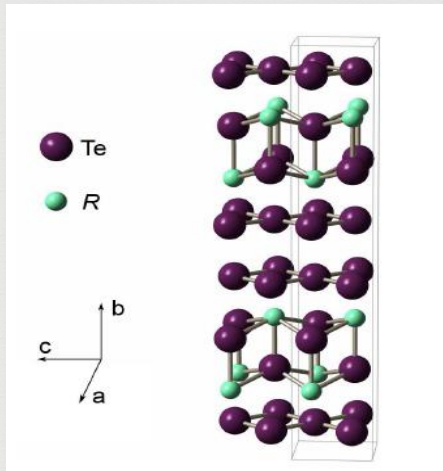


(R=Y, La, Ce, Nd, Sm, Gd, Tb, Ho, Dy, Er, Tm)

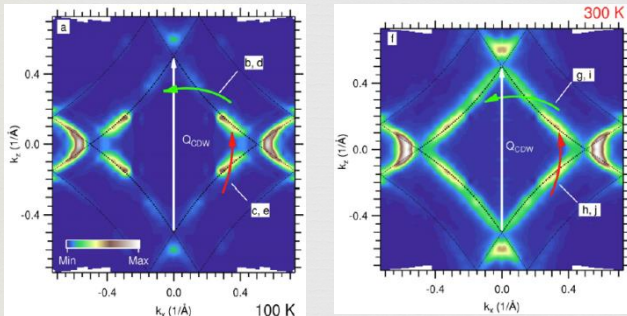
Layered quasi-two dimensional compounds

Crystal structure

– weak orthorhombic



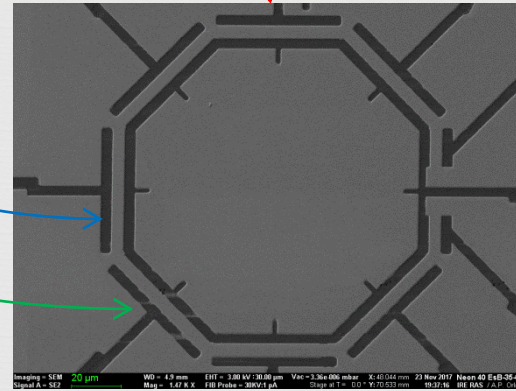
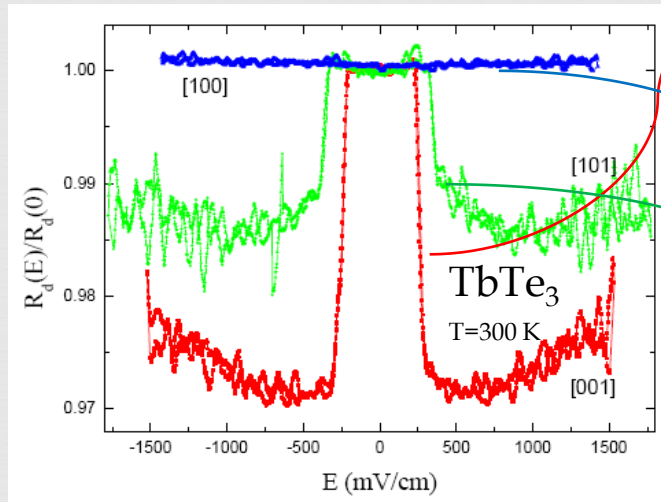
Fermi surface for TbTe₃.



Incommensurate CDW below the temperature T_{CDW1} through the whole R series with a wave vector $Q_{CDW1} = (0, 0, \sim 2/7c^*)$. For the heavier R (Dy, Ho, Er, Tm) atoms a second CDW occurs at low temperature T_{CDW2} with the wave vector $Q_{CDW2} = (\sim 2/7a^*, 0, 0)$ perpendicular to Q_{CDW1}

(F. Schmitt et al., New Journal of Physics 13, 063022, 2011)

CDW sliding



Sliding is possible only along the CDW wave vector

(SSC. 188, 67 (2014))

following $\frac{j_c}{f_0} = 2e$

number of chains per cross-section

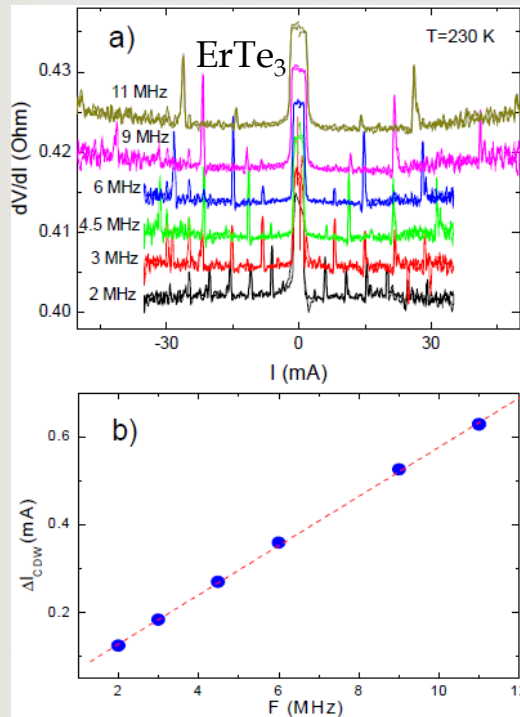
$$1.90 \times 10^8$$

number of unit-cells per cross-section-

$$1.96 \times 10^8$$

TbTe₃

→ *“hidden” 1D character*



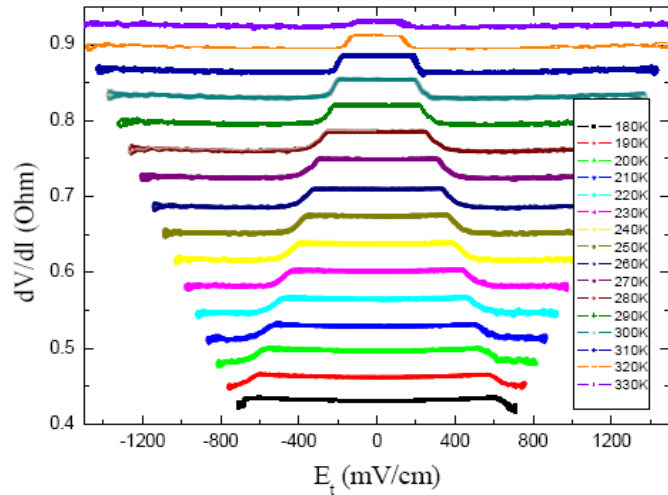
PRB, 93, 235141 (2016)

In contrast to 1D case

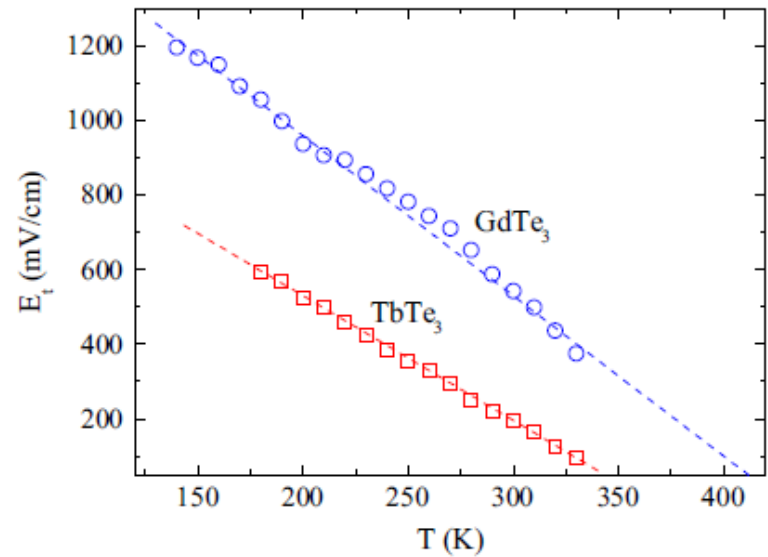
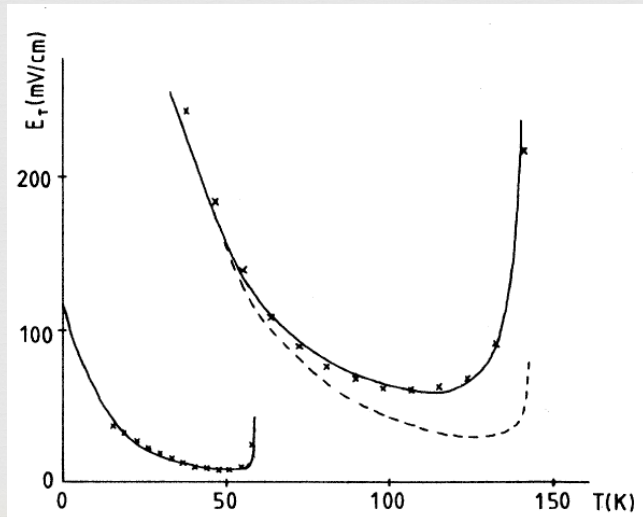
linear $E_t(T)$

$$E(T) = E(0)\left(1 - \frac{T}{T_0}\right)$$

$$T_0 \approx 1.08T_{CDW}$$



1D case - exponential dependence



K. Maki, PRB, 13, 9640 (1989)

NEW PUZZLING EFFECT IN THE CDW SLIDING -

- TIME EVOLUTION OF THE THRESHOLD ELECTRIC FIELD

E_t increases significantly if the sample is kept at a fixed T_{expt} below T_{CDW} a sufficiently long time.
(that was never observed in 1D system)

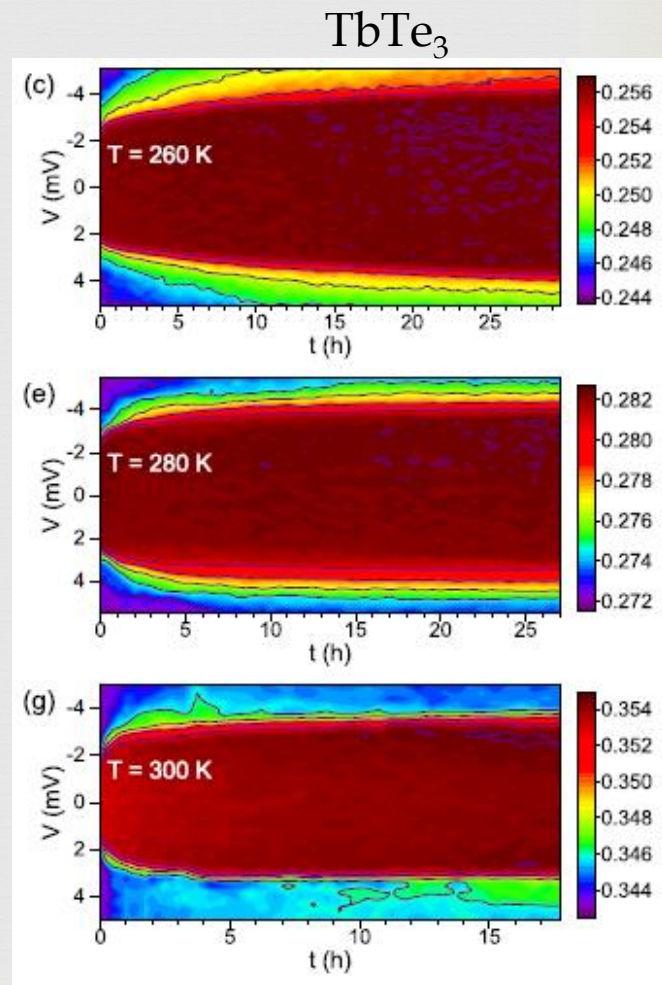
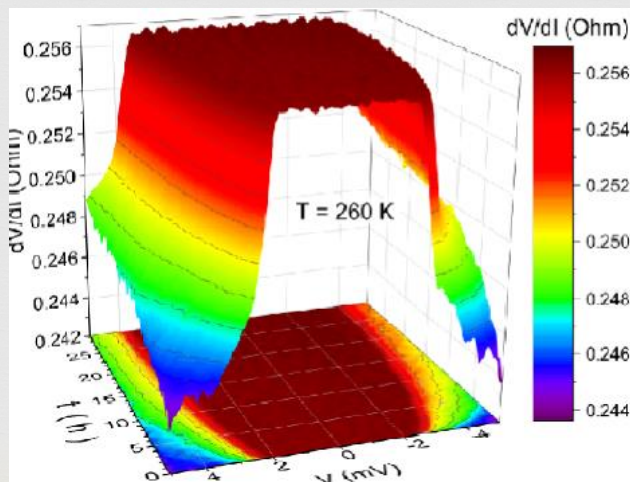
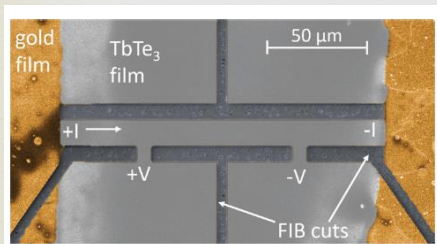
Procedure:

cooling the sample from $T > T_{CDW}$ down to a given temperature T_{expt} and measuring IV curves with a time interval of 30 minutes during several tens of hours

and

that at different T_{expt} in the range 220–330 K.

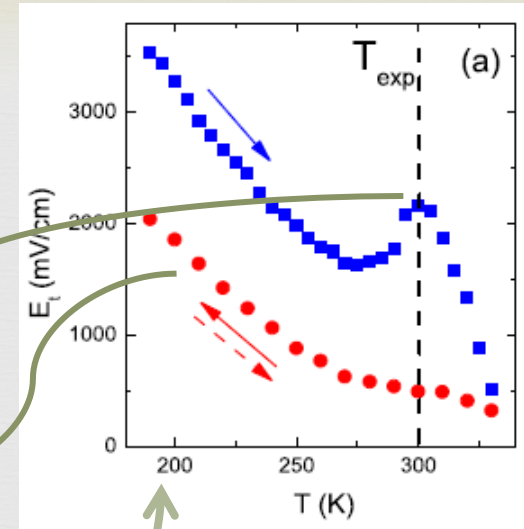
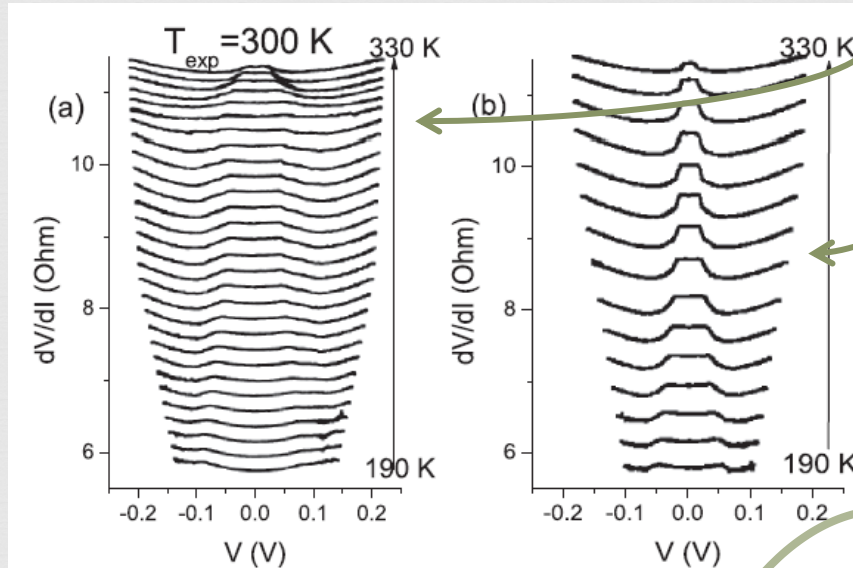
(below 220 K effect is very weak)



AFTER EXPOSITION (TbTe_3)

T-dependence of $E_t \longrightarrow$ *peak effect*

No any change in resistance and the CDW transition temperature



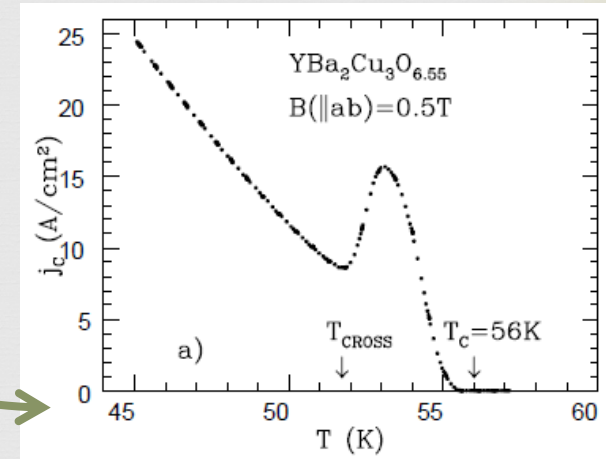
Like to superconductors?



Effect is completely reversible: the initial state can be easily restored by increase of temperature 20-30 K above T_{expt}

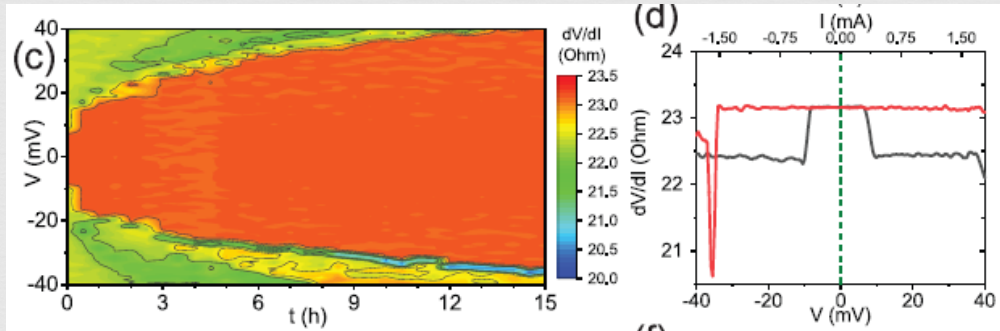
melting of what?

melting of Larkin domains

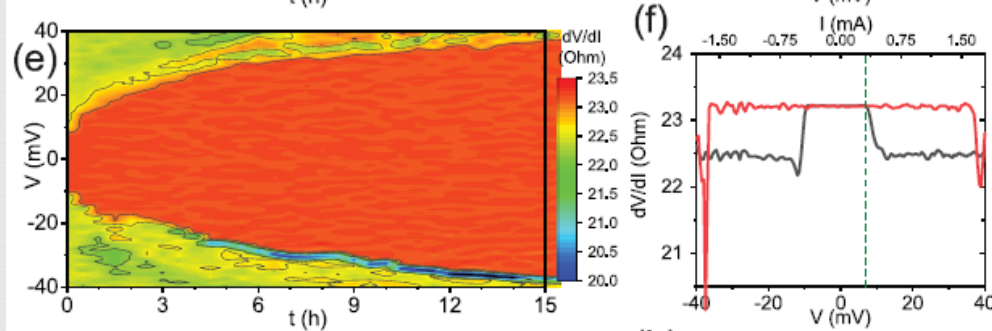


Exposure at different current state (TbTe_3)

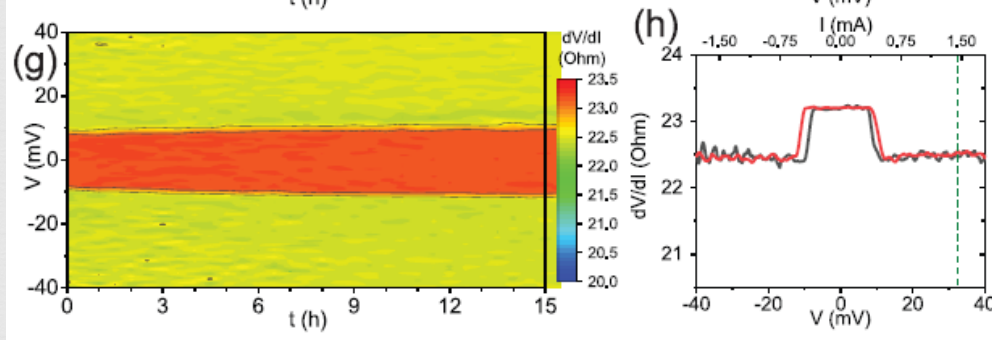
$I=0$



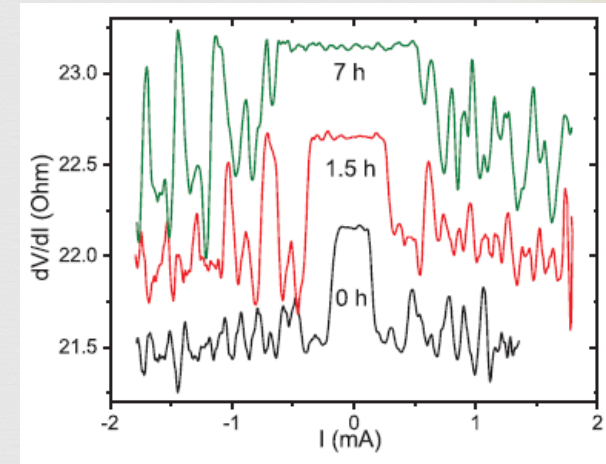
$I < I_{th}$



$I > I_{th}$

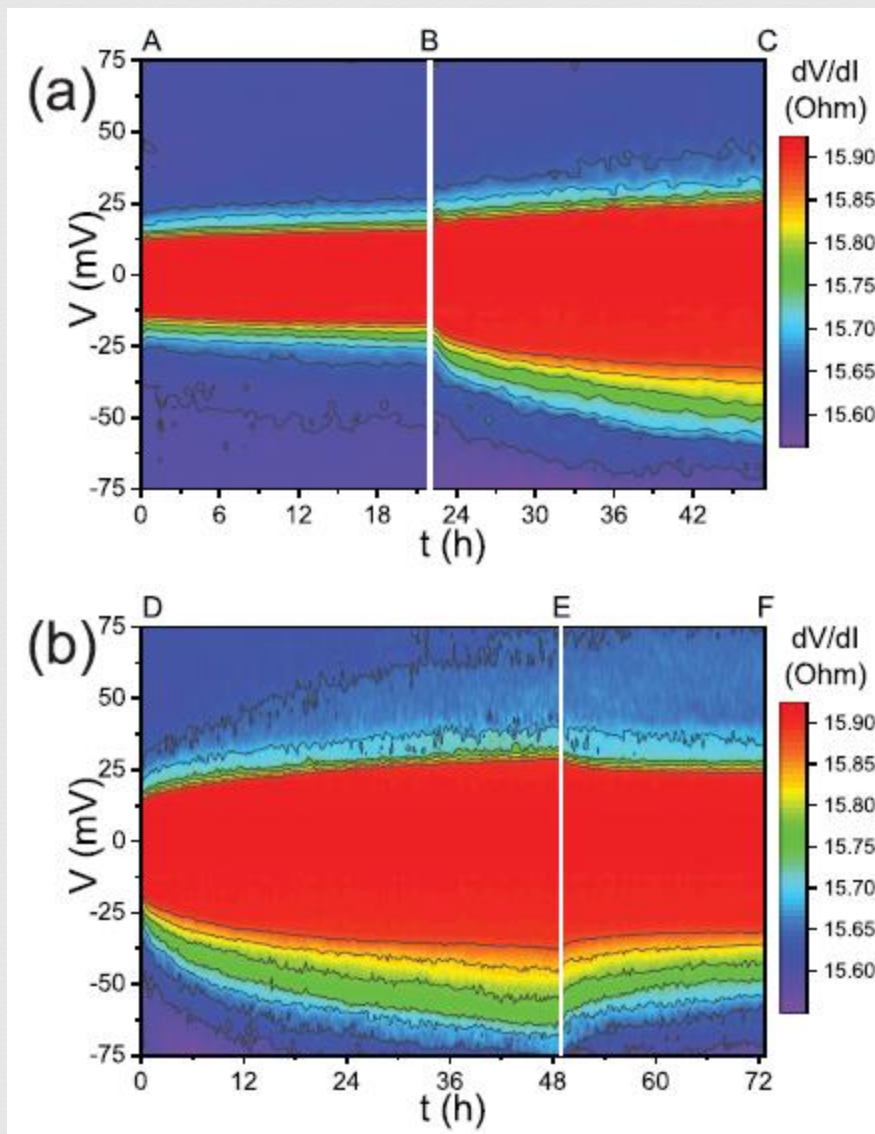


Shapiro steps structure improved under exposure



Time-effect is practically absent in the sliding state of CDW -
- something happens with the CDW sub-system.

280 K



being at a given thermodynamic parameters

+

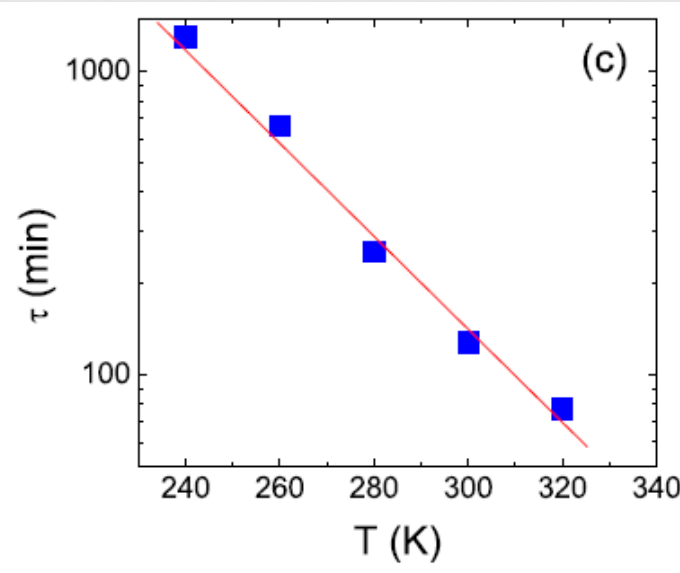
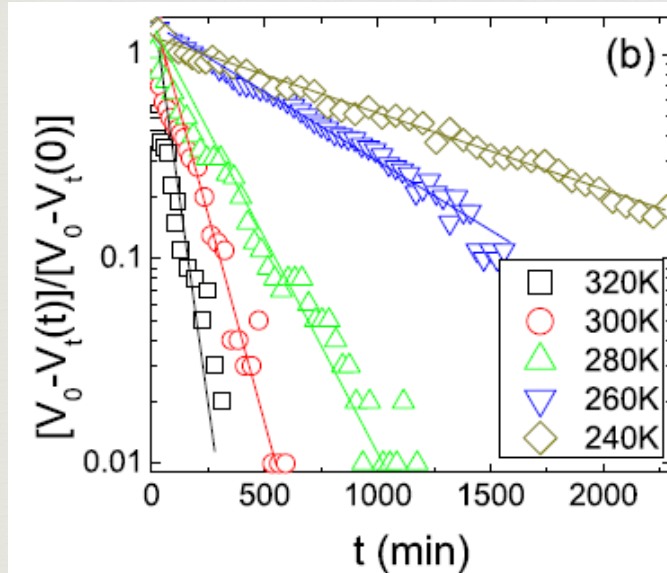
without external perturbations

the system tends to its ground state

Growth of E_t with time \longrightarrow relaxation to the ground state

Characteristic time parameters of such relaxation

Assuming exponential relaxation



$$\tau \sim \exp\left(-\frac{T}{T_0}\right)$$

$$T_0 \approx 30 \text{ K}$$

V_0 is saturating (?) value of the threshold voltage

Mobile impurities? → No

PHYSICAL REVIEW B

VOLUME 53, NUMBER 23

15 JUNE 1996-I

Dislocations and the motion of weakly pinned charge-density waves: Experiments on niobium triselenide containing mobile indium impurities

J. C. Gill

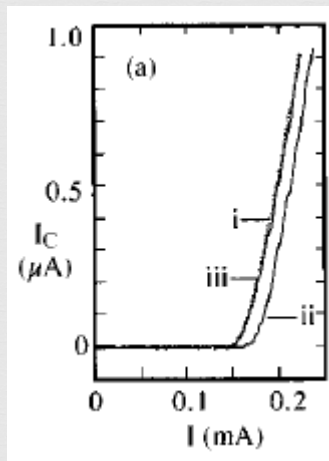
H. H. Wills Physics Laboratory, Tyndall Avenue, Bristol BS8 ITL, United Kingdom

(Received 31 October 1995; revised manuscript received 29 January 1996)

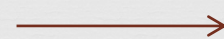
The I_n increases E_T by an amount δE_T ,

which is greatest when the CDW is at rest, and can be reduced almost to zero by its continuous motion.

TbTe₃ - no reduction to zero. Only stop of increase.



Increase of E_t -
less than 30%



In TbTe₃ - 1000%

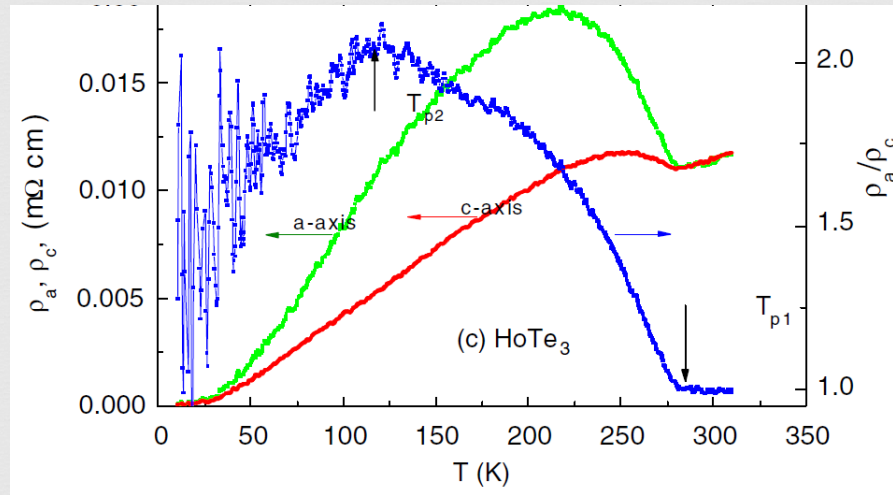
time taken for δE_T to adjust to a change in the state of the CDW (of the order of 1 s at 115 K)

In TbTe₃ - 10⁵ s at 240 K

No peak effect in NbSe₃

HoTe₃

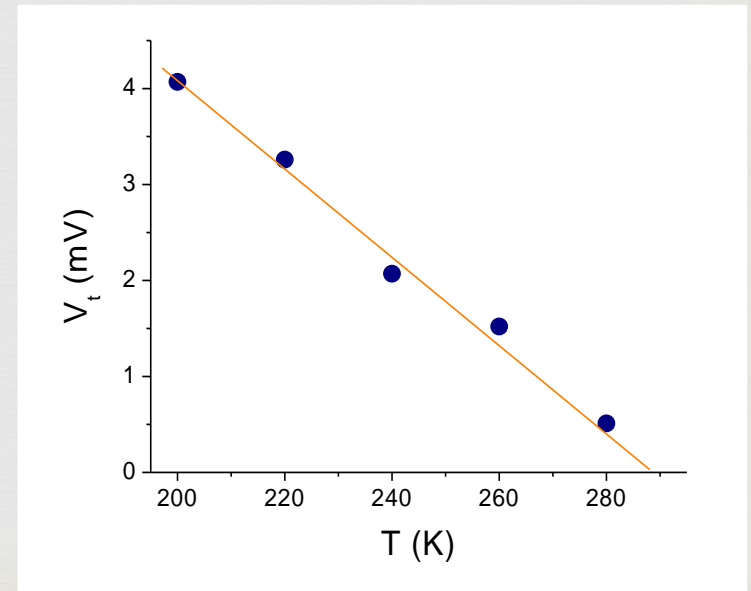
Two CDW transitions: $T_{\text{CDW1}}=285\text{ K}$ and $T_{\text{CDW2}}=110\text{ K}$



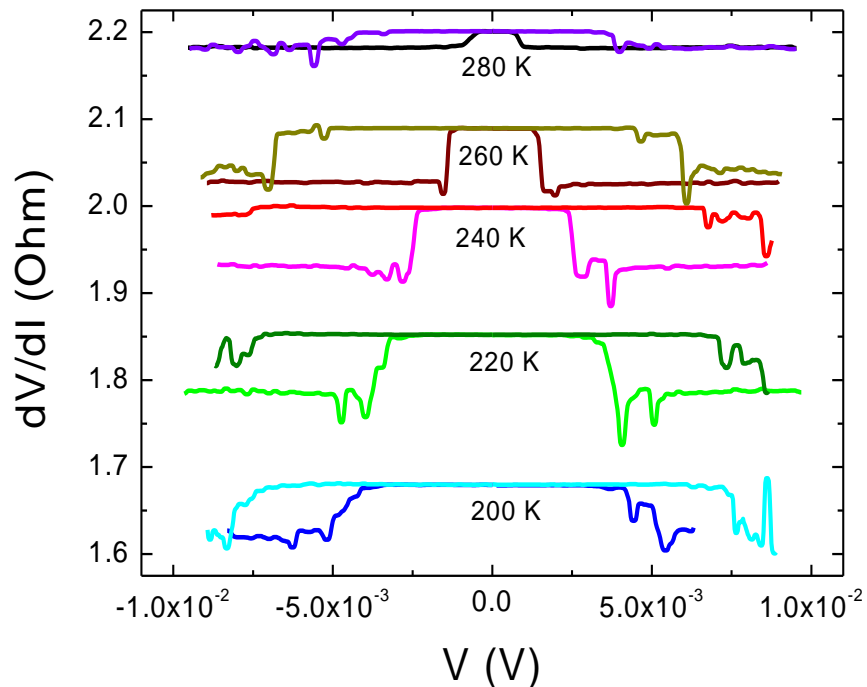
Never warmed above room temperature

Exposed at 280 K, 260 K,
240 K, 220 K and 200 K

before exposition $E_t(T)$



Studying this effect in HoTe_3 for exposure time up to 200 hours



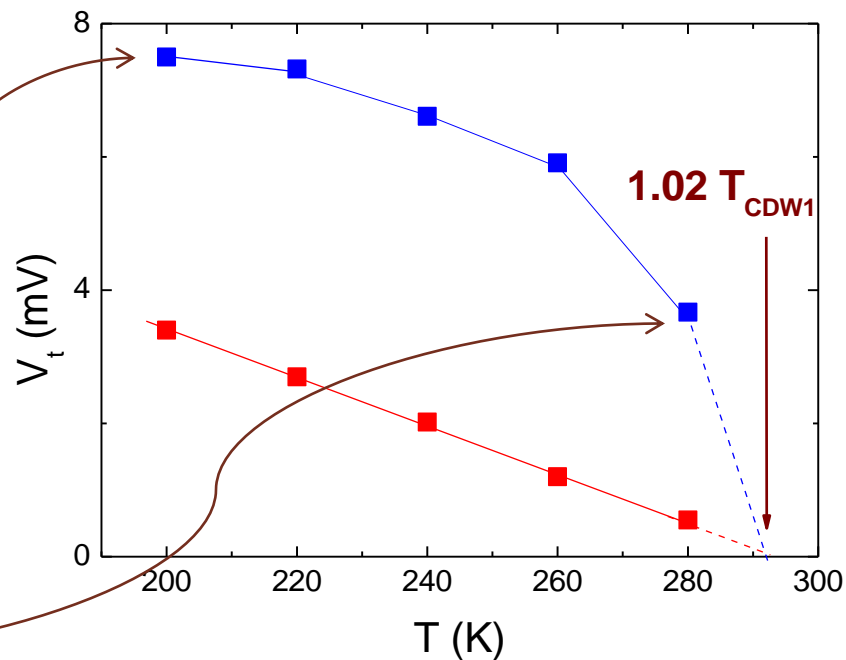
Initial and final differential IVs

~2 times

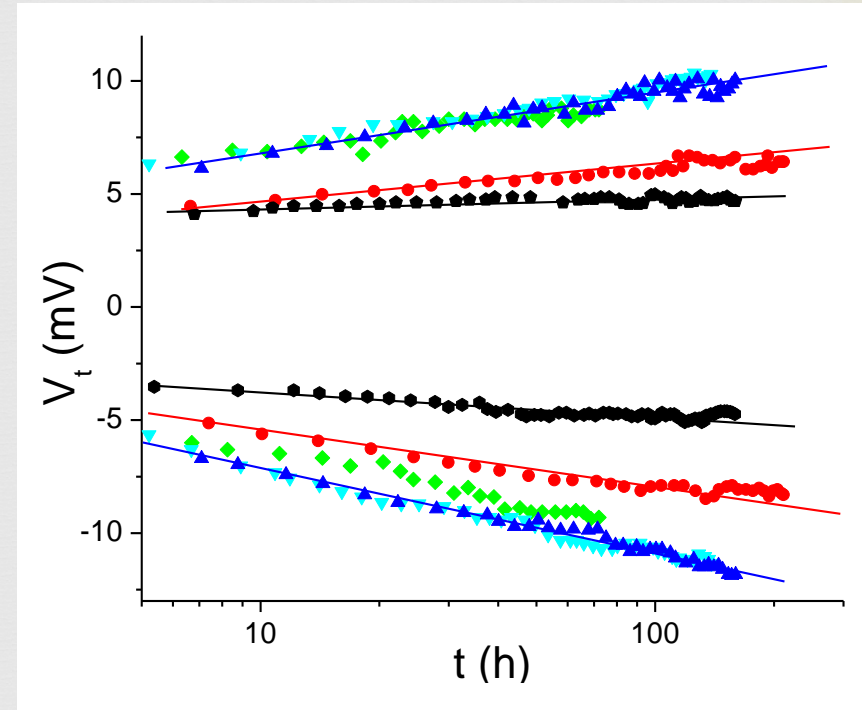
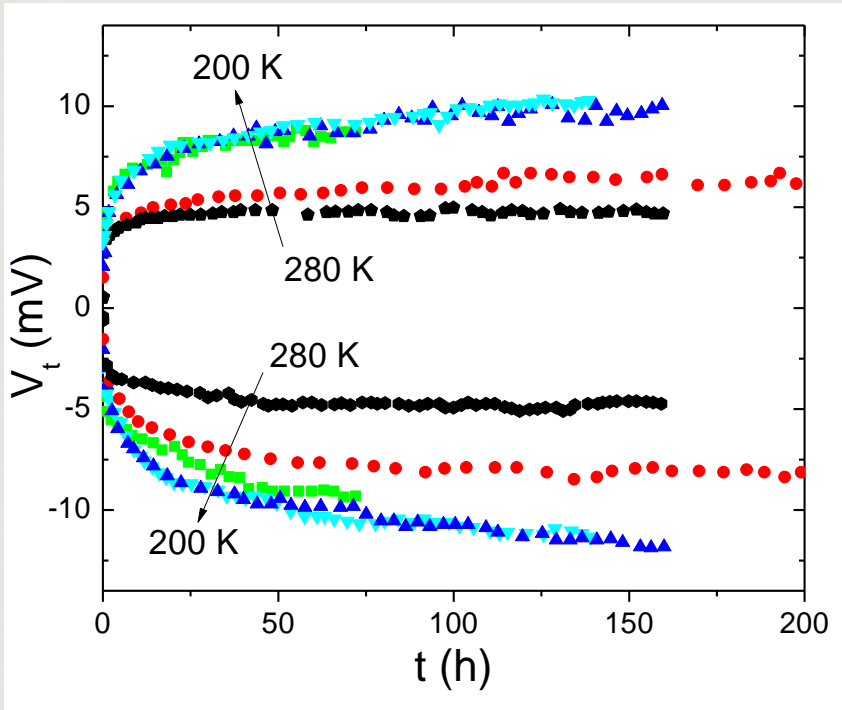
Initial and final $E_t(T)$



~10 times



TIME PARAMETERS



No saturation even after 150 hours

Linear dependence $E_t(\lg(t))$



GLASSY STATE

CONCLUSION

1. Demonstrating all features of the CDW sliding in quasi-1D systems, the CDW sliding in 2D compounds of $R\text{Te}_3$ family reveals specific features which are different from 1D case: linear dependence of $E_t(T)$; very low velocity of the CDW.
2. Most intriguing feature is time evolution of the threshold electric field. Something happens, but what?
3. Detail structure studying need to be done to understand that.

Thank you very much for attention